ReRAM is Real

Zhiqiang Wei

Panasonic Corporation

ReRAM

• Mechanism is still unclear

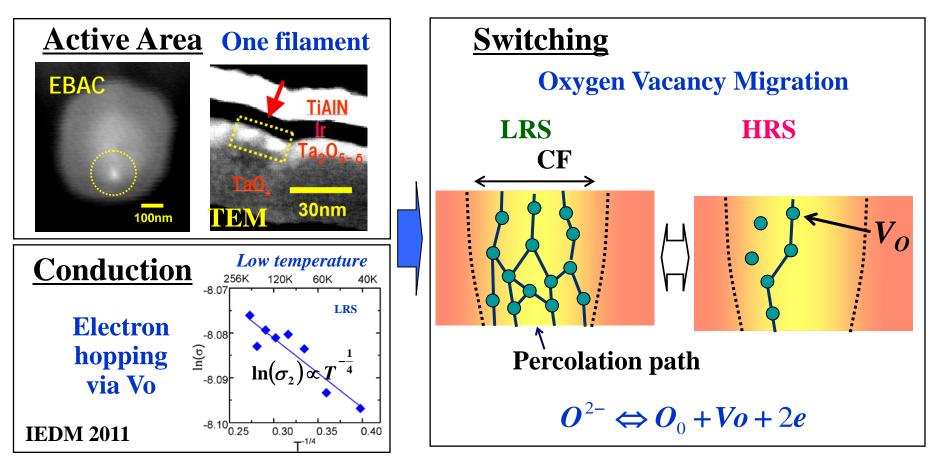
• Any oxide is switchable

• Emerging Memory



Switching Model for ReRAM

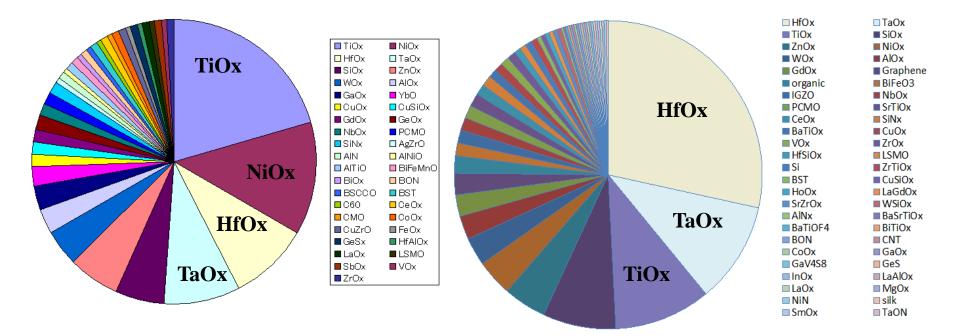
- Active area \rightarrow One filament in the Ta₂O_{5- δ} layer
- Conduction \rightarrow Electron hopping via oxygen vacancies
- Switching \rightarrow The change of the density of *Vo*



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Materials for ReRAM

- Various materials show resistance switching
- Number of TaOx-paper rises to No.2 in 2013



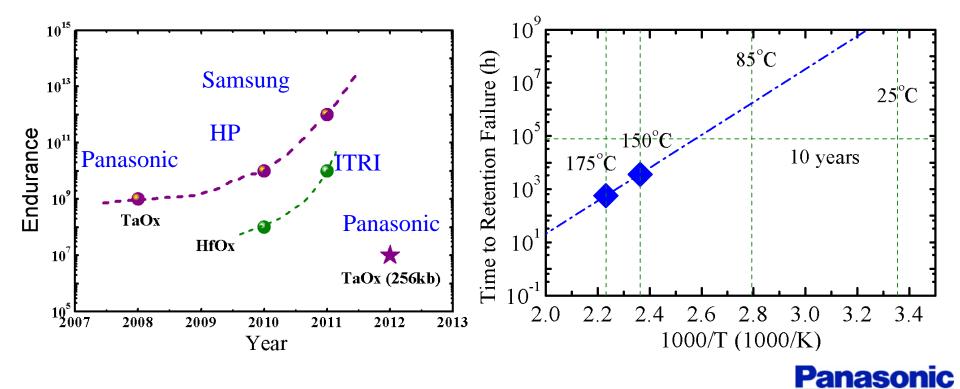
(Google scholar 2012.1-2012.12)

(Google scholar 2013.1-2013.12)

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TaOx ReRAM

- Long Endurance Capability of TaOx ReRAM
- Retention period of the 256-kbit array including tail bits is more than 10 years at 85°C.



ReRAM in the market

Panasonic has started world's first massproduction of ReRAM-embedded MCU since August 2013.

Jul 30, 2013

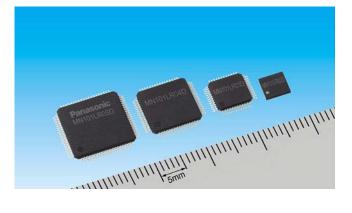
Panasonic Starts World's First Mass Production of ReRAM Mounted Microcomputers

About Panasonic Media Contacts

Osaka, Japan - Panasonic Corporation today announced that it will start the world's first*1 mass-production of microcomputers with mounted ReRAM [1], a type of non-volatile memory, in August 2013. Through utilizing microcomputers with mounted ReRAM, it

Panasonic will start mass production in August 2013 of the ReRAM mounted microcomputers, contributing to longer operational times for security, portable and energy harvesting equipment with low power consumption.

will be possible to achieve high-speed rewriting and longer operational times in battery-powered equipment, such as portable devices and security devices etc.,



Panasonic Corp. press release

We hope much further spread of ReRAM in the market!

Panasonic

Summary

Mechanism is still unclear Redox Reaction in Filament near Anode

Any oxide is switchable TaOx ReRAM shows high reliability

Emerging Memory
ReRAM is in the market

